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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, SD, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	66
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 32x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk24fn1m0vll12r

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Table 7. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
	entering all modes with the crystal enabled.	440	490	540	560	570	580	nA
	VLLS1	440	490	540	560	570	580	
	VLLS3	490	490	540	560	570	680	
	LLS	510	560	560	560	610	680	
	VLPS	510	560	560	560	610	680	
	STOP							
I _{48MIRC}	48 Mhz internal reference clock	350	350	350	350	350	350	μA
I _{CMP}	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.	22	22	22	22	22	22	μA
I _{RTC}	RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption.	432	357	388	475	532	810	nA
I _{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption.							μA
	MCGIRCLK (4 MHz internal reference clock)	66	66	66	66	66	66	
	OSCERCLK (4 MHz external crystal)	214	237	246	254	260	268	
I _{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	μA
I _{ADC}	ADC peripheral adder combining the measured values at V _{DD} and V _{DDA} by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	42	42	42	42	42	42	μA

2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

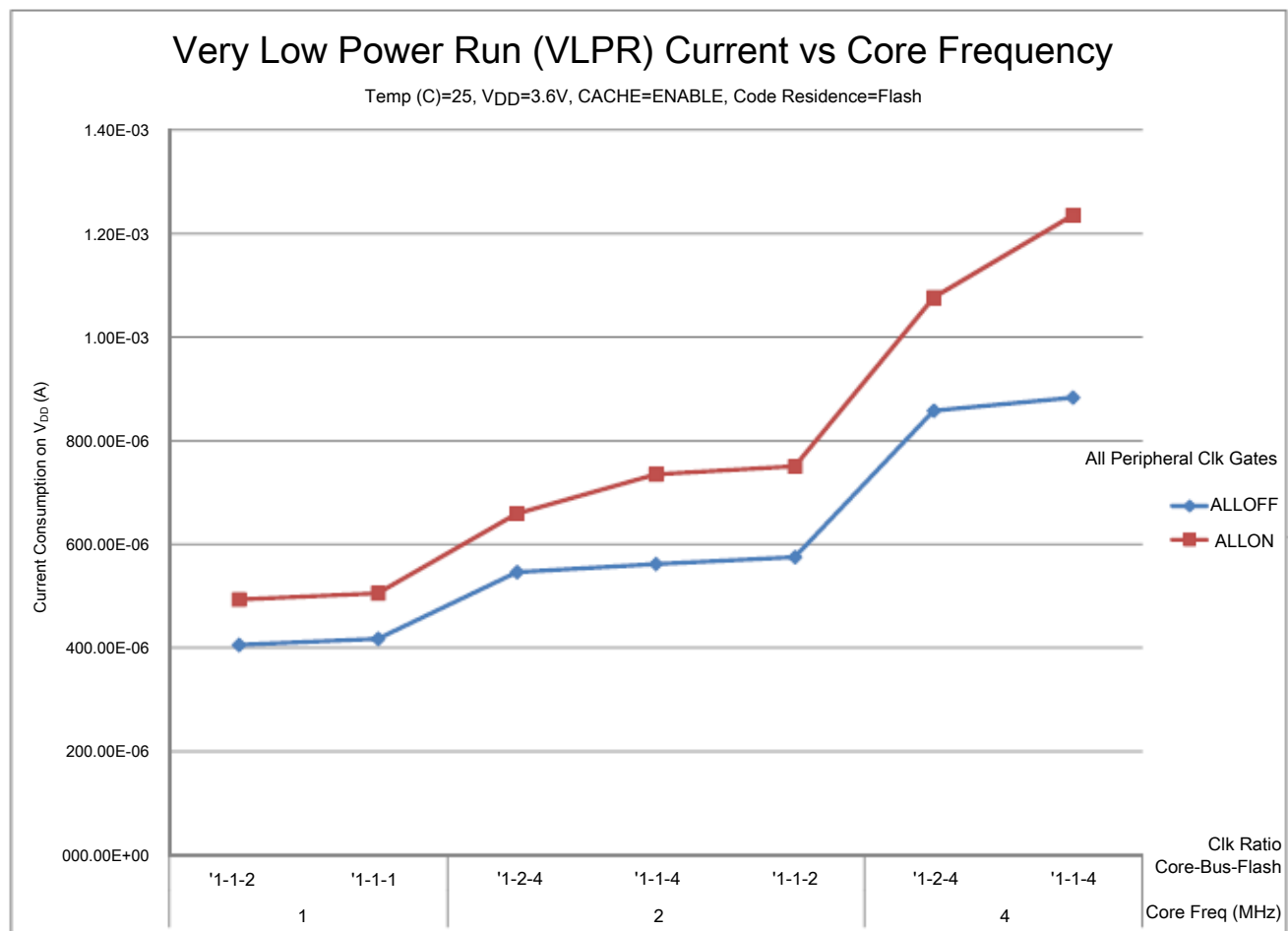


Figure 4. VLPR mode supply current vs. core frequency

2.2.6 EMC radiated emissions operating behaviors

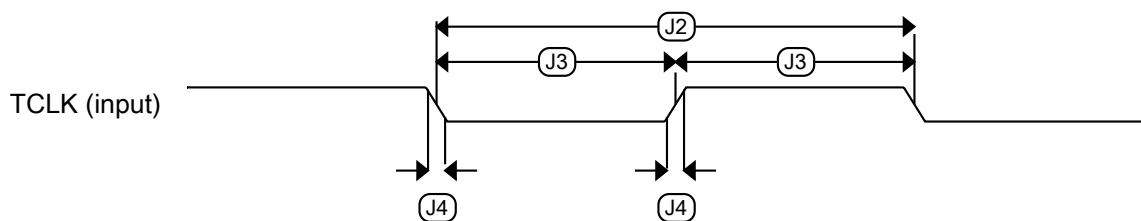
Table 8. EMC radiated emissions operating behaviors

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
			144 LQFP		
V _{RE1}	Radiated emissions voltage, band 1	0.15–50	16	dBμV	1, 2
V _{RE2}	Radiated emissions voltage, band 2	50–150	22	dBμV	
V _{RE3}	Radiated emissions voltage, band 3	150–500	21	dBμV	
V _{RE4}	Radiated emissions voltage, band 4	500–1000	16	dBμV	
V _{RE_IEC}	IEC level	0.15–1000	L	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and*

Table 16. JTAG full voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
J1	TCLK frequency of operation • Boundary Scan • JTAG and CJTAG • Serial Wire Debug	0 0 0	10 20 40	MHz
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width • Boundary Scan • JTAG and CJTAG • Serial Wire Debug	50 25 12.5	— — —	ns ns ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	2.9	—	ns
J11	TCLK low to TDO data valid	—	22.1	ns
J12	TCLK low to TDO high-Z	—	22.1	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

**Figure 7. Test clock input timing**

- Maximum time based on expectations at cycling end-of-life.

3.4.1.2 Flash timing specifications — commands

Table 24. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk512k}$	Read 1s Block execution time • 512 KB program flash	—	—	1.8	ms	
$t_{rd1sec4k}$	Read 1s Section execution time (4 KB flash)	—	—	100	μs	1
t_{pgmchk}	Program Check execution time	—	—	95	μs	1
t_{rdsrc}	Read Resource execution time	—	—	40	μs	1
t_{pgm8}	Program Phrase execution time	—	90	150	μs	
$t_{ersblk512k}$	Erase Flash Block execution time • 512 KB program flash	—	435	3700	ms	2
t_{ersscr}	Erase Flash Sector execution time	—	15	115	ms	2
$t_{rd1alln}$	Read 1s All Blocks execution time • Program flash only devices	—	—	3.4	ms	
t_{rdonce}	Read Once execution time	—	—	30	μs	1
$t_{pgmonce}$	Program Once execution time	—	70	—	μs	
t_{ersall}	Erase All Blocks execution time	—	870	7400	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
$t_{swapx01}$	Swap Control execution time • control code 0x01	—	200	—	μs	
$t_{swapx02}$	• control code 0x02	—	70	150	μs	
$t_{swapx04}$	• control code 0x04	—	70	150	μs	
$t_{swapx08}$	• control code 0x08	—	—	30	μs	

- Assumes 25MHz or greater flash clock frequency.
- Maximum times for erase parameters based on expectations at cycling end-of-life.

3.4.1.3 Flash high voltage current behaviors

Table 25. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	3.5	7.5	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 26. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
$t_{\text{nvmretp10k}}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{\text{nvmretp1k}}$	Data retention after up to 1 K cycles	20	100	—	years	
n_{nvmcycp}	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$.

3.4.2 EzPort switching specifications

Table 27. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{\text{SYS}}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{\text{SYS}}/8$	MHz
EP2	$\overline{\text{EZP_CS}}$ negation to next EZP_CS assertion	$2 \times t_{\text{EZP_CK}}$	—	ns
EP3	$\overline{\text{EZP_CS}}$ input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to $\overline{\text{EZP_CS}}$ input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—	18	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	$\overline{\text{EZP_CS}}$ negation to EZP_Q tri-state	—	12	ns

2. Specification is valid for all FB_AD[31:0] and $\overline{\text{FB_TA}}$.

Table 29. Flexbus full voltage range switching specifications

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	
	Frequency of operation	—	FB_CLK	MHz	
FB1	Clock period	1/FB_CLK	—	ns	
FB2	Address, data, and control output valid	—	13.5	ns	1
FB3	Address, data, and control output hold	0	—	ns	1
FB4	Data and $\overline{\text{FB_TA}}$ input setup	15.5	—	ns	2
FB5	Data and $\overline{\text{FB_TA}}$ input hold	0.5	—	ns	2

1. Specification is valid for all FB_AD[31:0], $\overline{\text{FB_BE/BWE}n}$, $\overline{\text{FB_CS}n}$, $\overline{\text{FB_OE}}$, $\overline{\text{FB_R/W}}$, $\overline{\text{FB_TBST}}$, FB_TSIZE[1:0], FB_ALE, and $\overline{\text{FB_TS}}$.
2. Specification is valid for all FB_AD[31:0] and $\overline{\text{FB_TA}}$.

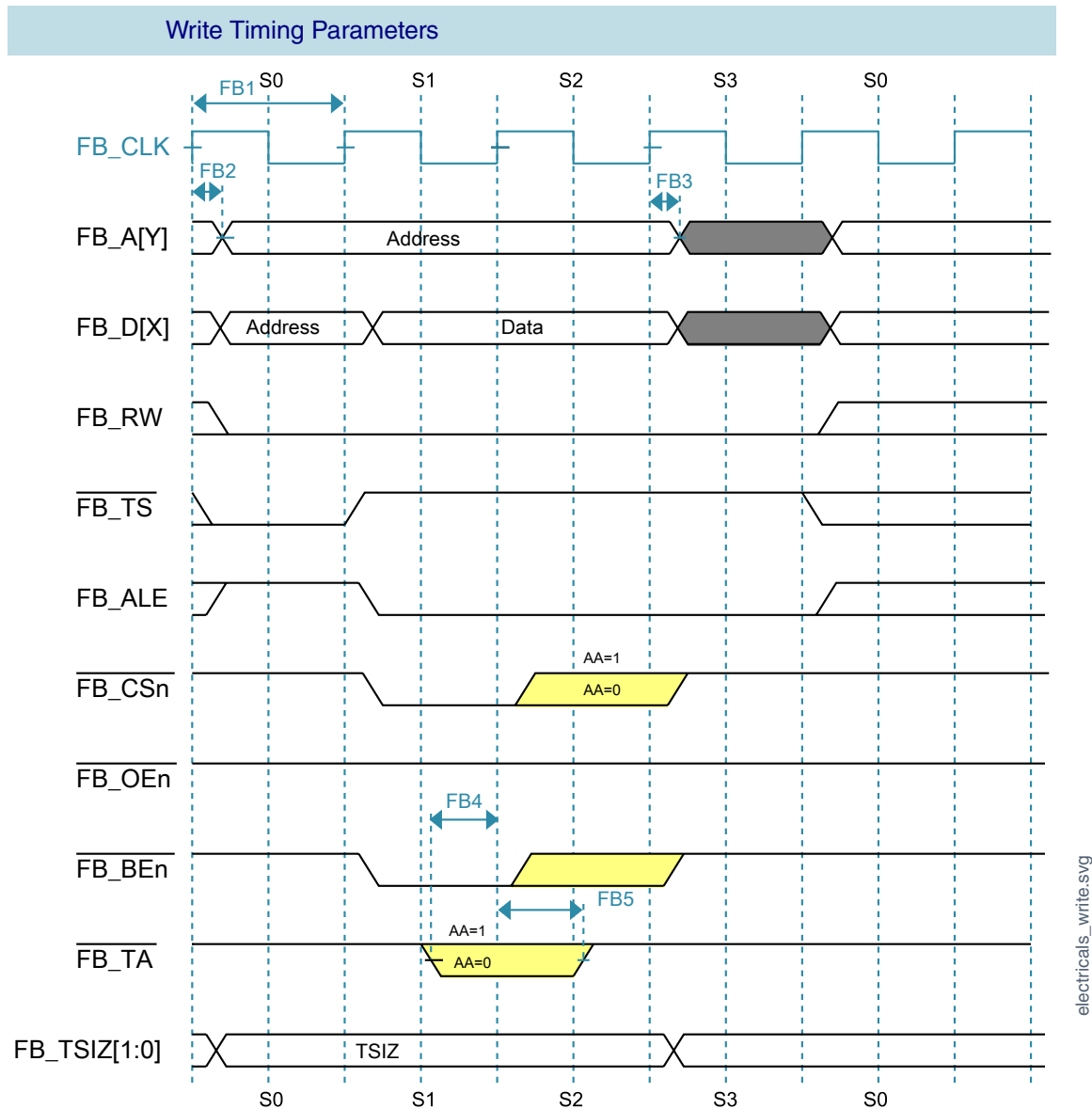


Figure 13. FlexBus write timing diagram

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in [Table 30](#) and [Table 31](#) are achievable on the differential pins ADCx_DP0, ADCx_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

3.6.1.1 16-bit ADC operating conditions

Table 30. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V _{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV _{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} – V _{DDA})	-100	0	+100	mV	2
ΔV _{SSA}	Ground voltage	Delta to V _{SS} (V _{SS} – V _{SSA})	-100	0	+100	mV	2
V _{REFH}	ADC reference voltage high		1.13	V _{DDA}	V _{DDA}	V	
V _{REFL}	ADC reference voltage low		V _{SSA}	V _{SSA}	V _{SSA}	V	
V _{ADIN}	Input voltage		V _{REFL}	—	V _{REFH}	V	
C _{ADIN}	Input capacitance	16-bit mode 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	
R _{ADIN}	Input series resistance		—	2	5	kΩ	
R _{AS}	Analog source resistance (external)	13-bit / 12-bit modes f _{ADCK} < 4 MHz	—	—	5	kΩ	3
f _{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	18.0	MHz	4
f _{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C _{rate}	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	ksps	5
C _{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	ksps	5

Table 31. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
TUE	Total unadjusted error	12-bit modes <12-bit modes	—	±4	±6.8	LSB ⁴	5
DNL	Differential non-linearity	12-bit modes <12-bit modes	—	±0.7	–1.1 to +1.9	LSB ⁴	5
INL	Integral non-linearity	12-bit modes <12-bit modes	—	±1.0	–2.7 to +1.9	LSB ⁴	5
E _{FS}	Full-scale error	12-bit modes <12-bit modes	—	–4	–5.4	LSB ⁴	V _{ADIN} = V _{DDA} ⁵
E _Q	Quantization error	16-bit modes ≤13-bit modes	—	–1 to 0	—	LSB ⁴	
ENOB	Effective number of bits	16-bit differential mode - Avg = 32 - Avg = 4 16-bit single-ended mode - Avg = 32 - Avg = 4	12.8 11.9	14.5 13.8	— —	bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	6.02 × ENOB + 1.76			dB	
THD	Total harmonic distortion	16-bit differential mode - Avg = 32 16-bit single-ended mode - Avg = 32	—	–94	—	dB dB	7
SFDR	Spurious free dynamic range	16-bit differential mode - Avg = 32 16-bit single-ended mode - Avg = 32	82	95	— —	dB dB	7
E _{IL}	Input leakage error		I _{in} × R _{AS}			mV	I _{in} = leakage current (refer to the MCU's voltage and

Table continues on the next page...

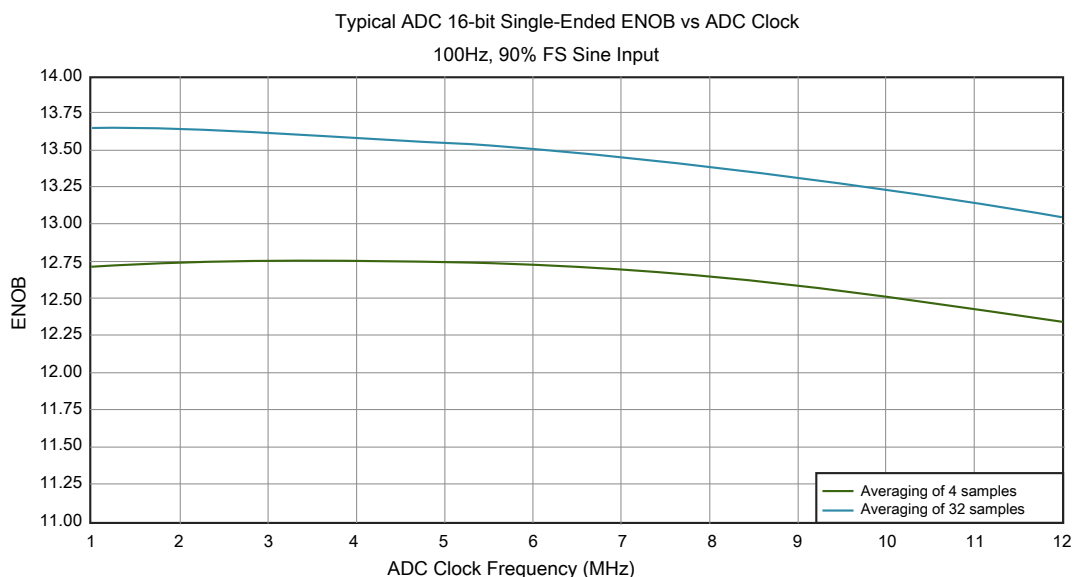


Figure 16. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

3.6.2 CMP and 6-bit DAC electrical specifications

Table 32. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μ A
$I_{DDL S}$	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μ A
V_{AIN}	Analog input voltage	$V_{SS} - 0.3$	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	$V_{DD} - 0.5$	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	—	—	40	μ s
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μ A
INL	6-bit DAC integral non-linearity	-0.5	—	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	-0.3	—	0.3	LSB

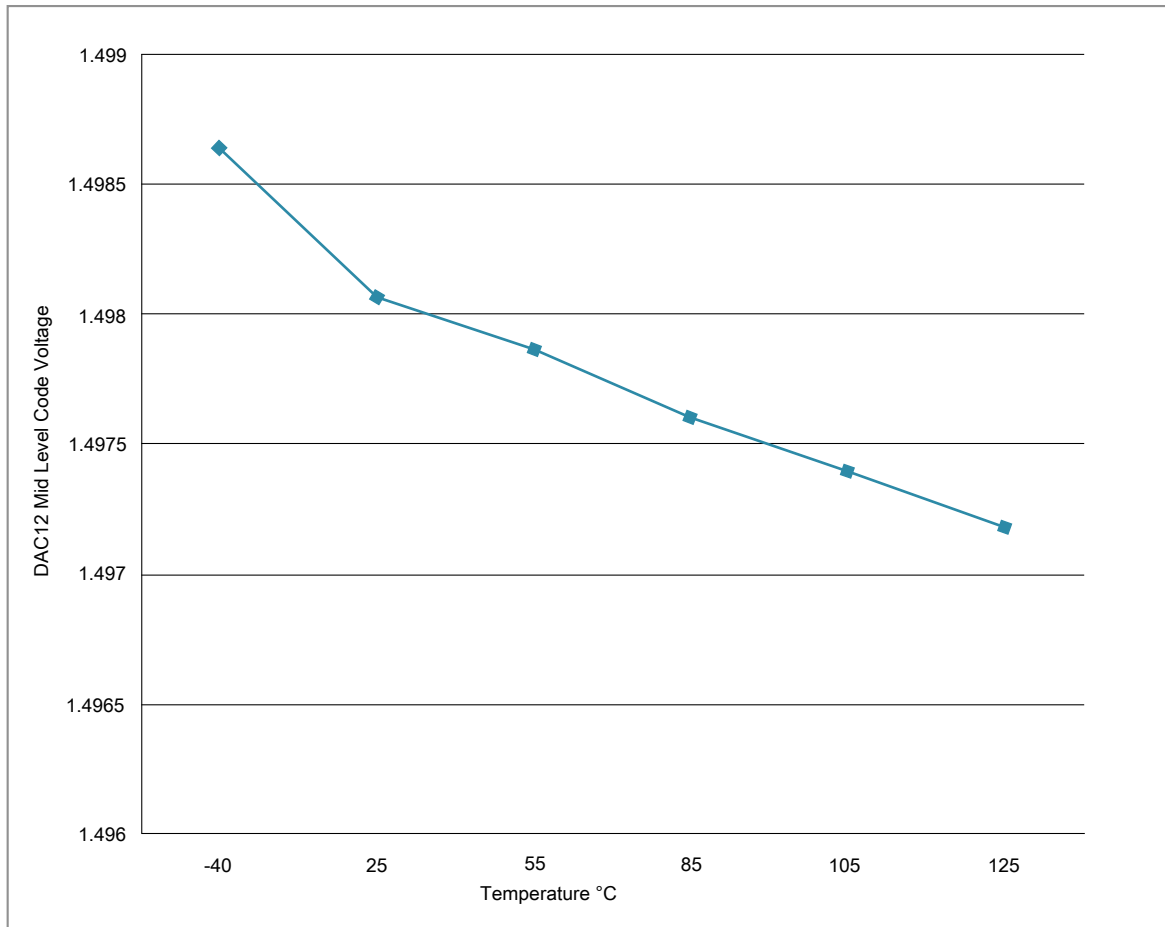


Figure 20. Offset at half scale vs. temperature

3.6.4 Voltage reference electrical specifications

Table 35. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	—
T_A	Temperature	Operating temperature range of the device		°C	—
C_L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

3.8.5 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 41. Master mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	30	MHz	
DS1	DSPI_SCK output cycle time	$2 \times t_{\text{BUS}}$	—	ns	
DS2	DSPI_SCK output high/low time	$(t_{\text{SCK}}/2) - 2$	$(t_{\text{SCK}}/2) + 2$	ns	
DS3	DSPI_PCSn valid to DSPI_SCK delay	$(t_{\text{BUS}} \times 2) - 2$	—	ns	1
DS4	DSPI_SCK to DSPI_PCSn invalid delay	$(t_{\text{BUS}} \times 2) - 2$	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-2	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	15	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

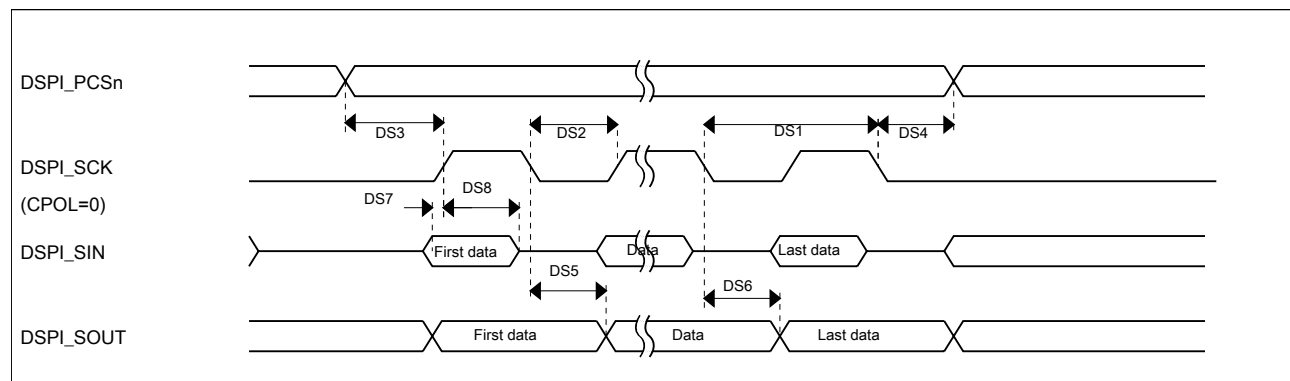


Figure 21. DSPI classic SPI timing — master mode

Table 42. Slave mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		15 ¹	MHz

Table continues on the next page...

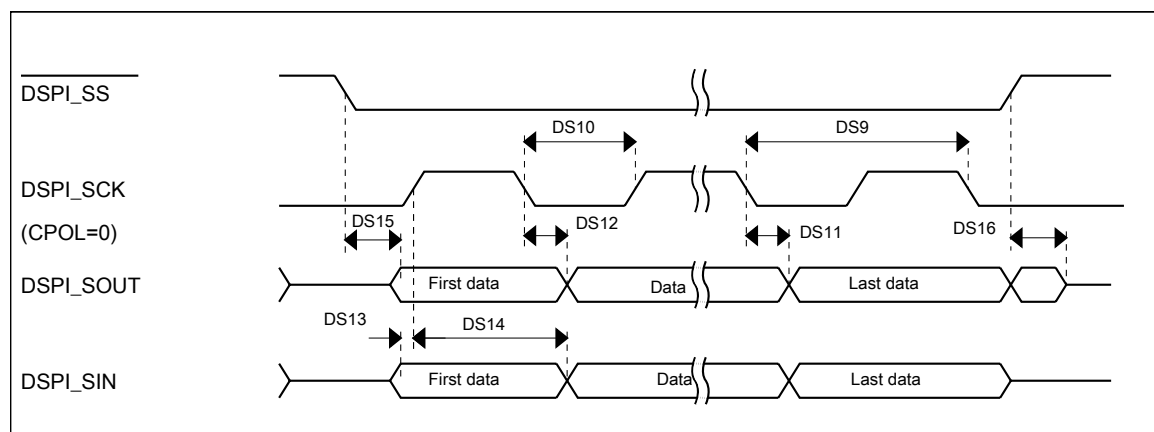


Figure 24. DSPI classic SPI timing — slave mode

3.8.7 Inter-Integrated Circuit Interface (I²C) timing

Table 45. I²C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f _{SCL}	0	100	0	400 ¹	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t _{HD} ; STA	4	—	0.6	—	μs
LOW period of the SCL clock	t _{LOW}	4.7	—	1.25	—	μs
HIGH period of the SCL clock	t _{HIGH}	4	—	0.6	—	μs
Set-up time for a repeated START condition	t _{SU} ; STA	4.7	—	0.6	—	μs
Data hold time for I ² C bus devices	t _{HD} ; DAT	0 ²	3.45 ³	0 ⁴	0.9 ²	μs
Data set-up time	t _{SU} ; DAT	250 ⁵	—	100 ^{3, 6}	—	ns
Rise time of SDA and SCL signals	t _r	—	1000	20 + 0.1C _b ⁷	300	ns
Fall time of SDA and SCL signals	t _f	—	300	20 + 0.1C _b ⁶	300	ns
Set-up time for STOP condition	t _{SU} ; STO	4	—	0.6	—	μs
Bus free time between STOP and START condition	t _{BUF}	4.7	—	1.3	—	μs
Pulse width of spikes that must be suppressed by the input filter	t _{SP}	N/A	N/A	0	50	ns

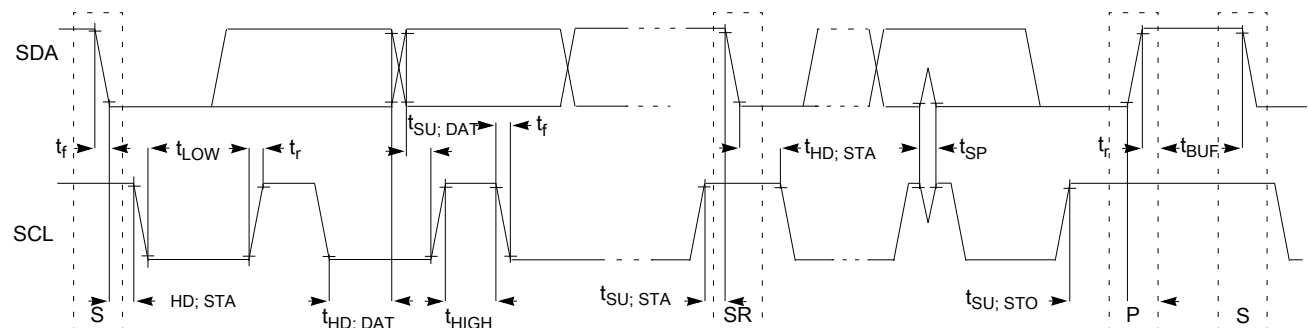
1. The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only be achieved when using the High drive pins across the full voltage range and when using the Normal drive pins and VDD ≥ 2.7 V.
2. The master mode I²C deasserts ACK of an address byte simultaneously with the falling edge of SCL. If no slaves acknowledge this address byte, then a negative hold time can result, depending on the edge rates of the SDA and SCL lines.
3. The maximum t_{HD}; DAT must be met only if the device does not stretch the LOW period (t_{LOW}) of the SCL signal.
4. Input signal Slew = 10 ns and Output Load = 50 pF
5. Set-up time in slave-transmitter mode is 1 IPBus clock period, if the TX FIFO is empty.

6. A Fast mode I²C bus device can be used in a Standard mode I²C bus system, but the requirement $t_{\text{SU; DAT}} \geq 250$ ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line $t_{\text{rmax}} + t_{\text{SU; DAT}} = 1000 + 250 = 1250$ ns (according to the Standard mode I²C bus specification) before the SCL line is released.
7. C_b = total capacitance of the one bus line in pF.

Table 46. I²C 1 Mbps timing

Characteristic	Symbol	Minimum	Maximum	Unit
SCL Clock Frequency	f_{SCL}	0	1 ¹	MHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	$t_{\text{HD; STA}}$	0.26	—	μs
LOW period of the SCL clock	t_{LOW}	0.5	—	μs
HIGH period of the SCL clock	t_{HIGH}	0.26	—	μs
Set-up time for a repeated START condition	$t_{\text{SU; STA}}$	0.26	—	μs
Data hold time for I ² C bus devices	$t_{\text{HD; DAT}}$	0	—	μs
Data set-up time	$t_{\text{SU; DAT}}$	50	—	ns
Rise time of SDA and SCL signals	t_r	$20 + 0.1C_b$ ²	120	ns
Fall time of SDA and SCL signals	t_f	$20 + 0.1C_b$ ²	120	ns
Set-up time for STOP condition	$t_{\text{SU; STO}}$	0.26	—	μs
Bus free time between STOP and START condition	t_{BUF}	0.5	—	μs
Pulse width of spikes that must be suppressed by the input filter	t_{SP}	0	50	ns

1. The maximum SCL clock frequency of 1 Mbps can support maximum bus loading when using the High drive pins across the full voltage range.
2. C_b = total capacitance of the one bus line in pF.

**Figure 25. Timing definition for devices on the I²C bus**

3.8.8 UART switching specifications

See [General switching specifications](#).

3.8.9 SDHC specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

Table 47. SDHC switching specifications

Num	Symbol	Description	Min.	Max.	Unit
		Operating voltage	1.71	3.6	V
Card input clock					
SD1	fpp	Clock frequency (low speed)	0	400	kHz
	fpp	Clock frequency (SD\SDIO full speed\high speed)	0	25\50	MHz
	fpp	Clock frequency (MMC full speed\high speed)	0	20\50	MHz
	f _{OD}	Clock frequency (identification mode)	0	400	kHz
SD2	t _{WL}	Clock low time	7	—	ns
SD3	t _{WH}	Clock high time	7	—	ns
SD4	t _{TLH}	Clock rise time	—	3	ns
SD5	t _{THL}	Clock fall time	—	3	ns
SDHC output / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)					
SD6	t _{OD}	SDHC output delay (output valid)	-5	8.3	ns
SDHC input / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)					
SD7	t _{ISU}	SDHC input setup time	5.5	—	ns
SD8	t _{IH}	SDHC input hold time	0	—	ns

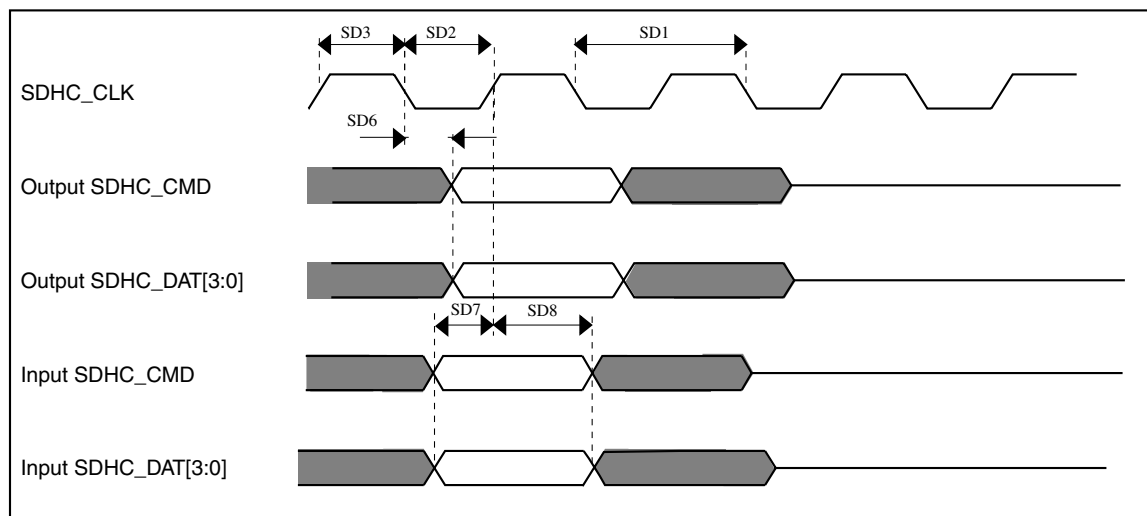


Figure 26. SDHC timing

144 QFP	100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	ALT8	ALT9
68	46	DISABLED		PTA16	SPI0_SOUT	UART0_CTS_b/ UART0_COL_b	RMII0_TXD0/ MII0_TXD0		I2S0_RX_FS	I2S0_RXD1			
69	47	ADC1_SE17	ADC1_SE17	PTA17	SPI0_SIN	UART0_RTS_b	RMII0_TXD1/ MII0_TXD1		I2S0_MCLK				
70	48	VDD	VDD										
71	49	VSS	VSS										
72	50	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0					EXTAL0	
73	51	XTAL0	XTAL0	PTA19		FTM1_FLT0	FTM_CLKIN1		LPTMR0_ALT1			LPTMR0_ALT1	
74	52	RESET_b	RESET_b									RESET_b	
75	—	DISABLED		PTA24			MII0_TXD2		FB_A29				
76	—	DISABLED		PTA25			MII0_TXCLK		FB_A28				
77	—	DISABLED		PTA26			MII0_TXD3		FB_A27				
78	—	DISABLED		PTA27			MII0_CRS		FB_A26				
79	—	DISABLED		PTA28			MII0_TXER		FB_A25				
80	—	DISABLED		PTA29			MII0_COL		FB_A24				
81	53	ADC0_SE8/ ADC1_SE8	ADC0_SE8/ ADC1_SE8	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0	RMII0_MDIO/ MII0_MDIO		FTM1_QD_PHA			LLWU_P5	
82	54	ADC0_SE9/ ADC1_SE9	ADC0_SE9/ ADC1_SE9	PTB1	I2C0_SDA	FTM1_CH1	RMII0_MDC/ MII0_MDC		FTM1_QD_PHB				
83	55	ADC0_SE12	ADC0_SE12	PTB2	I2C0_SCL	UART0_RTS_b	ENET0_1588_TMR0		FTM0_FLT3				
84	56	ADC0_SE13	ADC0_SE13	PTB3	I2C0_SDA	UART0_CTS_b/ UART0_COL_b	ENET0_1588_TMR1		FTM0_FLT0				
85	—	ADC1_SE10	ADC1_SE10	PTB4			ENET0_1588_TMR2		FTM1_FLT0				
86	—	ADC1_SE11	ADC1_SE11	PTB5			ENET0_1588_TMR3		FTM2_FLT0				
87	—	ADC1_SE12	ADC1_SE12	PTB6				FB_AD23					
88	—	ADC1_SE13	ADC1_SE13	PTB7				FB_AD22					
89	—	DISABLED		PTB8		UART3_RTS_b		FB_AD21					

Terminology and guidelines

Field	Description	Values
R	Silicon revision	• Z = Initial • (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = -40 to 105 • C = -40 to 85
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • FT = 48 QFN (7 mm x 7 mm) • LF = 48 LQFP (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm) • MP = 64 MAPBGA (5 mm x 5 mm) • LK = 80 LQFP (12 mm x 12 mm) • LL = 100 LQFP (14 mm x 14 mm) • MC = 121 MAPBGA (8 mm x 8 mm) • DC = 121 XFBGA (8 mm x 8 mm x 0.5 mm) • LQ = 144 LQFP (20 mm x 20 mm) • MD = 144 MAPBGA (13 mm x 13 mm)
CC	Maximum CPU frequency (MHz)	• 5 = 50 MHz • 7 = 72 MHz • 10 = 100 MHz • 12 = 120 MHz • 15 = 150 MHz • 16 = 168 MHz • 18 = 180 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

7.4 Example

This is an example part number:

MK24FN1M0VLQ12

8 Terminology and guidelines

8.1 Definitions

Key terms are defined in the following table:

Term	Definition
Rating	A minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

Table continues on the next page...

Term	Definition
	• <i>Operating ratings</i> apply during operation of the chip. • <i>Handling ratings</i> apply when the chip is not powered. NOTE: The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.
Operating requirement	A specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip
Operating behavior	A specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions
Typical value	A specified value for a technical characteristic that: • Lies within the range of values specified by the operating behavior • Is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions NOTE: Typical values are provided as design guidelines and are neither tested nor guaranteed.

8.2 Examples

Operating rating:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	−0.3	1.2	V

Operating requirement:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	0.9	1.1	V

Operating behavior that includes a typical value:

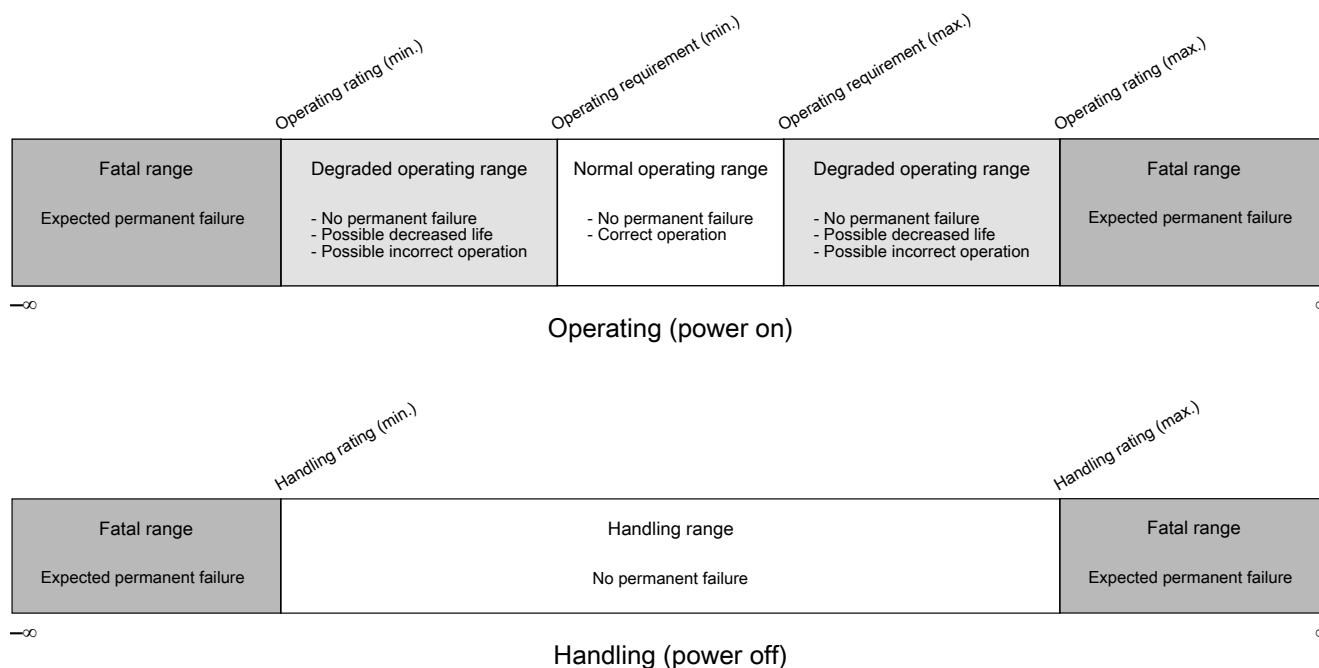
Symbol	Description	Min.	Typ.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μA

8.3 Typical-value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	Supply voltage	3.3	V

8.4 Relationship between ratings and operating requirements



8.5 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.